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# Compact Self-Packaged Low-Loss SISL LPF Using Symmetric Tri-Section SIRs

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**Abstract**—In this paper, a compact self-packaged dc-40GHz substrate integrated suspended line (SISL) low pass filter (LPF) with the flexibly controllable cutoff frequency  $f_c$  is proposed using symmetric tri-section stepped impedance resonators (ST-SIRs). The ST-SIR structure with low pass response is investigated theoretically and numerically. Moreover, a sharp roll-off rate performance is obtained by loading the L type center-symmetric spurlines which introduces controllable multiple transmission zeros (TZs). To further enhance the stopband performance of the LPF, the defected ground structures (DGS) integrated on the SISL are demonstrated. By surrounding with metallic vias and using the shielding layer of SISL, the radiation loss can be effectively reduced. For demonstration, a LPF prototype with a maximum in-band insertion loss ( $IL$ ) of 1.85 dB, an in-band return loss ( $RL$ ) of more than 14.8dB, an out-of-band suppression of larger than 17.2dB (from 43GHz-67GHz), and a size of  $0.41\lambda_g \times 0.69\lambda_g \times 0.44\lambda_g$  is fabricated and measured. The measured and simulated results are in good agreement.

**Index Terms**— Compact, low loss, LPF, SISL, ST-SIRs

## I. INTRODUCTION

WITH the rapid development of 5G/6G communications, the demand for wideband applications surges, which puts forward more stringent requirements for mm-wave circuits today [1], [2]. In particular, low pass filters (LPFs) play a crucial role in suppressing harmonics and spurious signals in complex systems with multiple mixing and frequency multiplication stages [3]. Therefore, there is an urgent need for LPFs with compact sizes, low insertion losses, high frequency selectivity and wide stopband.

Recently, some LPFs with high performance have been reported [4-6], [10], [12]. In [5], by employing asymmetric Pi-shaped Defected Ground Structure (DGS), the low-pass filter achieved a sharp roll-off performance, but with a narrower passband range. In [8], a waveguide LPF in X-band with low loss and high out-of-band suppression level is proposed, but the waveguide structure is hard to integrate with other planar circuits. Commonly, step impedance resonators (SIR) [7], [8]

are used to design compact filters. However, the excellent performance of SIR filters based on microstrip circuits at low frequencies will be greatly deteriorated in mm-wave bands. To comply with the requirement of high performance and integration, the type of substrate integrated lines has been widely concerned nowadays [9]. Ref. [10] demonstrates a dc-30 GHz LPF with compact size by using spoof surface plasmon polariton (SSPP) structure based on substrate integrated coaxial line (SICL), but the insertion loss ( $IL$ ) reaches 2.1 dB. In [11], substrate-integrated suspended line (SISL) technology based on standard printed circuit board (PCB) manufacturing process is proposed. Owing to its advantages of low loss, light weight, high integration and self-packaging performance, it has been widely used in designing high performance filters [12]-[14]. In [12], an 11th-order generalized Chebyshev SISL LPF with a cutoff frequency of 18 GHz is demonstrated, which shows the possibilities of SISL in ultra-wideband circuit design. However, when designing larger bandwidth components, the method using high-order filters is relatively complex. In [13], a miniaturized SISL bandpass filter is proposed with an  $IL$  of 1.6 dB at Ka-band, which demonstrates that SISL still has an excellent performance with low loss in the mm-wave band. Choi et al. in [15] proposed a compact wide-stopband LPFs design using SIR. This design controls the frequency response by adjusting the parameters of SIRs, achieving a wide stopband and compact size, which has a clear advantage in space-limited applications. However, this wide-stopband design may increase manufacturing complexity and may be affected by material properties and manufacturing tolerances in high-frequency performance. In [16], Zhang et al. extended the filter's stopband by integrating triple-mode resonators, enhancing the filter's selectivity. This design offers more design flexibility to meet the needs of specific applications, which is a significant advantage. However, integrating multi-mode resonators may increase the difficulty of design and tuning, and there may be issues of increased cost and complexity. Bakhtiar and Al-Husseini's research [17] achieves miniaturization of LPFs

This work is supported in part by the National Key R&D Program of China under Grant No. 2018YFB1801502, in part by the National Natural Science Foundation of China under Grant 61801059, in part by the FY2021 JSPS Postdoctoral Fellowship for Research in Japan under Grant P21053, and in part by the Grant-in-Aid for JSPS Research Fellow under Grant 21F21053, in part by the Basic Research and Frontier Exploration Special of Chongqing Natural Science Foundation under Grant cstc2019jcyj-msxmX0350.

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through the use of Complementary Split-Ring Resonators (CSRRs). This design offers significant advantages in space saving and integration, particularly in mobile and portable devices. However, the CSRR design may require precise manufacturing processes to ensure the desired electromagnetic performance, which could increase production costs and complexity. Ryu et al. [18] propose a 60-GHz bandpass filter using Asymmetric Stepped-Impedance Resonators (ASIRs), providing a high-performance filtering solution for 5G applications. This design meets the high-frequency and wide bandwidth requirements of 5G technology, but it may face challenges in material loss, potentially affecting its performance across a broader frequency range. Singh et al. [19] present a Substrate Integrated Waveguide (SIW) low-pass filter integrated with a DGS, demonstrating excellent performance in millimeter-wave applications. This design effectively suppresses unwanted modes and enhances filter selectivity, but the integration of DGS may increase design complexity and sensitivity to manufacturing tolerances. Li et al. [20] offer a compact LPF design using stub-loaded resonators, maintaining good performance while achieving miniaturization. However, the design of stub-loaded resonators may require precise dimensional control to ensure the filter's correct resonance, which could limit design flexibility. Kim et al. [21] propose a dual-band low-pass filter design that achieves dual-frequency filtering through asymmetric loading technology, potentially advantageous in multi-frequency applications. However, this design may require a complex tuning process to ensure filtering performance across both frequency bands, increasing the difficulty in design and manufacturing.

In this paper, a dc-40 GHz LPF by using symmetric tri-section stepped impedance resonators (ST-SIRs) based on self-packaged SISL platform is proposed. The cutoff frequency  $f_c$  can be flexibly adjusted by changing the physical sizes of the ST-SIRs. To improve the frequency selectivity of the LPF, a pair of center-symmetric L-type spurlines is loaded on SISL transmission line, which introduces additional transmission zeros (TZs) near the passband side and realizes a sharp roll-off skirt performance. The DGSs are loaded on top and bottom substrates of SISL to further broaden the stopband performance. The detailed analysis and design are in section II. Manufactured prototype and measured results are in section III.

## II. ANALYSIS AND DESIGN OF THE SISL LPF

As shown in Fig. 1, the proposed SISL LPF consists of a five-layer dielectric substrate. The top and bottom surfaces of each dielectric substrate are covered with copper layers (G1-G10). With the exception of Sub3, which uses Rogers 5880 (with  $h_3 = 0.254\text{mm}$ ,  $\epsilon_r = 2.2$ ,  $\tan\delta_d = 0.0009$ ), the other layers are low cost FR4 substrates (with  $h_1 = h_2 = h_4 = h_5 = 0.4\text{mm}$ ,  $\epsilon_r = 4.4$ ,  $\tan\delta_d = 0.02$ ). Sub2 and Sub4 are hollowed out to form air cavities, with the cavity width  $a = 3.5\text{ mm}$ , length  $b = 1.5\text{ mm}$ , and height  $H = h_2 + h_3 + h_4$ . Sub1 and Sub5 construct effective electromagnetic (EM) shielding boundaries. The suspended line circuit is mainly laid on copper layer G5. DGS structures are symmetrically integrated on copper layer G2 and G10, respectively.

### A. Analysis of symmetrical tri-section SIRs

The proposed LPF circuit structure with loaded ST-SIRs based on SISL platform is shown in Fig. 2(a). Two  $\lambda/4$  tri-section SIRs are symmetric about the  $y$ -axis, which are loaded on a horizontal inductance suspended line to achieve low pass response. As illustrated in Fig. 2(b), the tri-section SIR consists of three transmission lines with electrical lengths  $\theta_1$ ,  $\theta_2$ , and  $\theta_3$ , and the corresponding impedances are  $Z_1$ ,  $Z_2$ , and  $Z_3$ , respectively. According to Ref. [22], [23], the input impedance  $Z_{in}$  of the tri-section SIR can be expressed as:

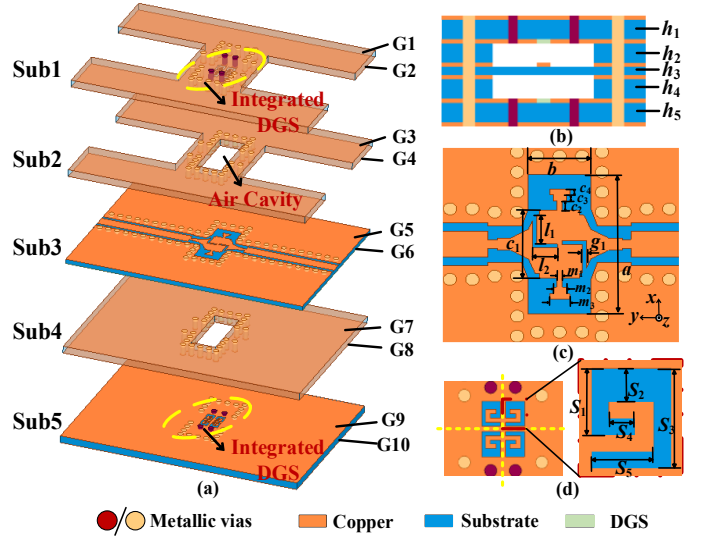


Fig. 1. Structure of the proposed LPF based on SISL platform. (a) 3D view, (b) cross view, (c) main circuit on Sub3, (d) details of the integrated DGS structure.

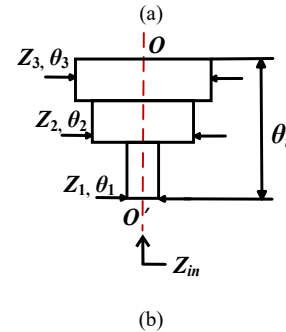
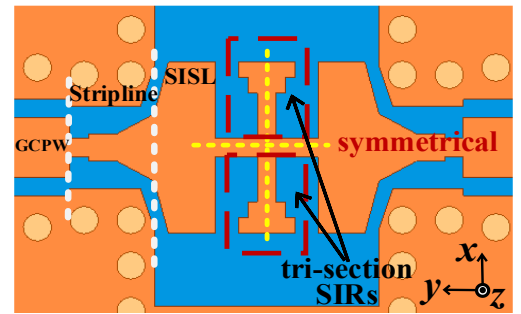


Fig. 2. (a) Original circuit of LPF loading ST-SIRs, and (b) geometry of  $\lambda/4$  tri-section SIR.

$$Z_{in} = jZ_2 \frac{-K_1 + \tan \theta_2 \tan \theta_3 + \frac{\tan \theta_1}{K_2} (\tan \theta_3 + K_1 \tan \theta_2)}{\tan \theta_3 + K_1 \tan \theta_2 + K_1 K_2 \tan \theta_1 - K_2 \tan \theta_1 \tan \theta_2 \tan \theta_3} \quad (1)$$

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where  $K_1=Z_3/Z_2$ ,  $K_2=Z_2/Z_1$  represent impedance ratios.

To simplify the analysis,  $\theta_1=\theta_2=\theta_3=\theta$  of the tri-section SIR has been set. When it is resonant, the expression between  $\theta$ , the resonance frequencies ( $f_1, f_2, f_3$ ) and the impedance ratios ( $K_1, K_2$ ) can be derived as:

$$\theta = \tan^{-1} \left( \sqrt{\frac{K_1 K_2}{K_1 + K_2 + 1}} \right) \quad (2)$$

$$K_1 = \frac{Z_3}{Z_2} = \frac{\tan^2 \left( \frac{\pi f_1}{2 f_3} \right) \left[ 1 + \tan^2 \left( \frac{\pi f_2}{2 f_3} \right) \right]}{1 + \tan^2 \left( \frac{\pi f_1}{2 f_3} \right)} \quad (3)$$

$$K_2 = \frac{Z_2}{Z_1} = \frac{K_1 + 1}{\tan^2 \left( \frac{\pi f_2}{2 f_3} \right) - K_1} \quad (4)$$

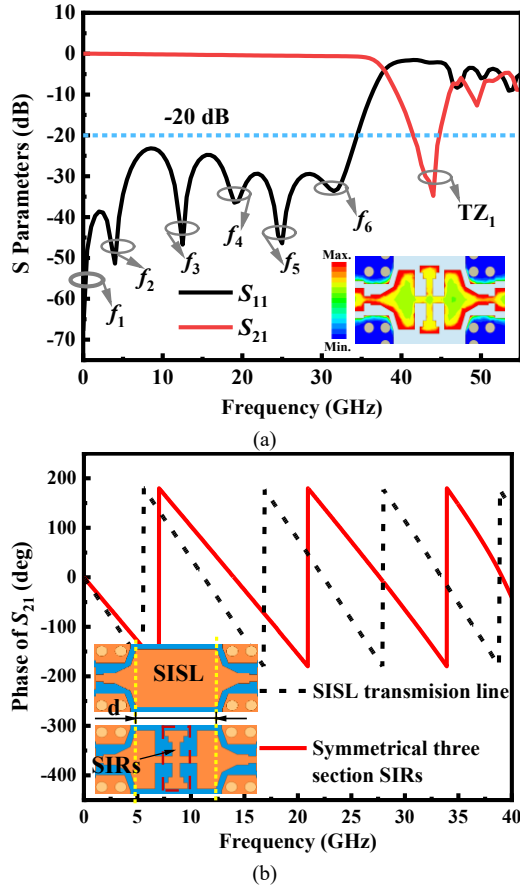


Fig. 3. (a) The low pass filtering response of symmetric tri-section SIRs, and (b) slow wave properties of ST-SIRs.

According to formulas (1)-(4), it can be known the resonant frequencies can be flexibly controlled by adjusting the physical size of tri-section SIR. For ST-SIRs, the total electrical length  $\theta_{st} = \theta_1 + \theta_2 + \theta_3$  [22], which corresponds to six resonant frequencies  $f_i$  ( $i = 1, 2, 3, \dots, 6$ ) as depicted in Fig. 3(a). And the ST-SIRs demonstrate a substantial low pass filtering response in Fig. 3(a). From Fig. 3(b), it's evident that compared to SISL transmission lines with the same length ( $d = 2\text{mm}$ ), the ST-SIRs

exhibit pronounced slow wave characteristics. It enables a more compact size for the device by adjusting the ST-SIRs' parameters. Moreover, some key parameters affecting the cutoff frequency  $f_c$  of LPF are also investigated numerically.

As illustrated in Fig. 4(a), it's apparent that when the parameter  $c_2$  is varied from 1.2mm to 0.6mm, the cut-off frequency  $f_c$  shifts towards higher frequencies. Similarly, in Fig. 4(b), as the parameter  $m_3$  changes from 1.1mm to 0.5mm, the cut-off frequency  $f_c$  also moves towards higher frequencies. It demonstrates that the proposed ST-SIRs LPF has flexibly controllable cut-off frequency.

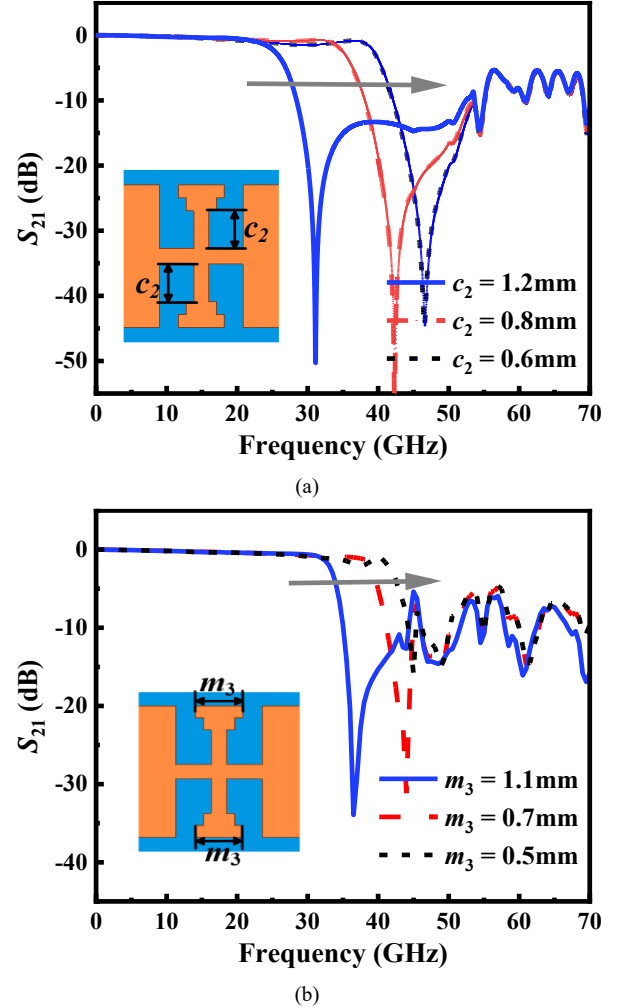


Fig. 4. Parameters affecting the cutoff frequency  $f_c$  of ST-SIRs LPF. (a) simulated  $S_{21}$  variations versus  $c_2$  and (b) simulated  $S_{21}$  variations versus  $m_3$ .

### B. Center-symmetric spurlines and DGS integrated on SISL

To further enhance the frequency selectivity of the filter, a pair of center-symmetric L-type spurlines are incorporated into the proposed LPF structure in subsection A, as illustrated in Fig. 5(a). The spurline resonator can be equivalent to a parallel RLC resonant circuit because of its bandgap property [24], as demonstrated in Fig. 5(b). The slotted gap capacitance is equivalent to the capacitance  $C$  of the resonator, while the slot line can be approximated as an inductance  $L$  of the resonator.

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Moreover, the current vector  $\mathbf{J}$  distribution of the LPF with loaded center-symmetric spurlines is shown in Fig. 5(c). It is evident that by employing two center-symmetric spurlines, named spurline ① and spurline ②, two current paths rotating counterclockwise and clockwise, respectively, are introduced, which create multiple TZs close to the passband as shown in Fig. 6.

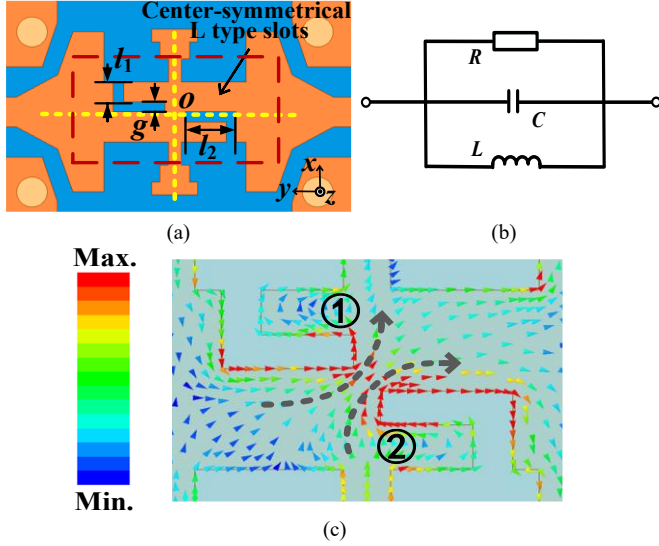


Fig. 5. (a) Geometry of center-symmetric spurlines, (b) equivalent circuit of spurlines, and (c) current vector  $\mathbf{J}$  distributions of center-symmetric spurlines.

Notably, the incorporation of center-symmetric spurlines results in a sharp roll-off performance, the roll-off rate ( $S_{21}$  from -3dB to -20dB) is improved nearly 10 times compared to the original structure in Fig. 2(a). It is worth noting that the lengths ( $l_1$  and  $l_2$ ) and the gap width ( $g_1$ ) of the spurlines are the key impact parameters. Consequently, the TZs outside the passband and the roll-off rate of the LPF can be flexibly tuned by changing the lengths  $l_1$  and  $l_2$  of the spurlines as investigated in Fig. 7. It can be seen from Fig. 7(a) that as the parameter  $l_1$  varies from 0.1mm to 0.3mm, TZ<sub>1</sub> gradually moves away from the passband side and towards higher frequencies, while TZ<sub>3</sub> moves towards lower frequencies, exhibiting a deeper out-of-band rejection level. Similarly, as depicted in Fig. 7(b), when the parameter  $l_2$  varies from 0.5mm to 0.7mm, all the TZs gradually approach the passband side, accompanied by an increased out-of-band rejection. Consequently, the frequency selectivity of the LPF can be effectively improved by flexibly controlling the position of the TZs.

The stopband performance is another important performance of LPF. It can be seen that the bandwidth of stopband is only ranging from 40.2 to 45.5 GHz. By cascading multiple DGS units to broaden the stopband of filters in microstrip circuits has been commonly used [5]. However, it will not only increase the size of the components, but also the radiation loss will increase greatly because the ground is destroyed, especially in mm-wave frequency. The substrate integrated defected ground structure (SIDGS) [25] has been reported recently as an effective method to reduce radiation loss due to DGS. Inspired by SIDGS and combining the advantages of high design freedom of multi-layer and self-shielded characteristics of SISL, two pairs of

DGS structures are symmetrically integrated on layer G2 and G10 of SISL, as shown in Fig. 1(a) and (d), respectively.

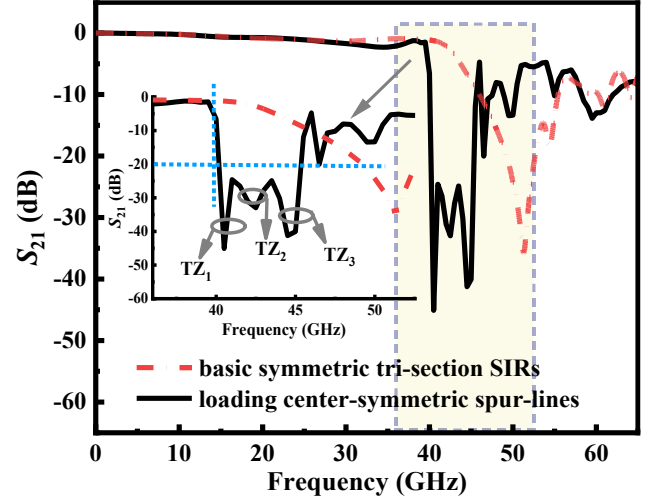


Fig. 6. Comparison of  $S_{21}$  with and without center-symmetric spurlines.

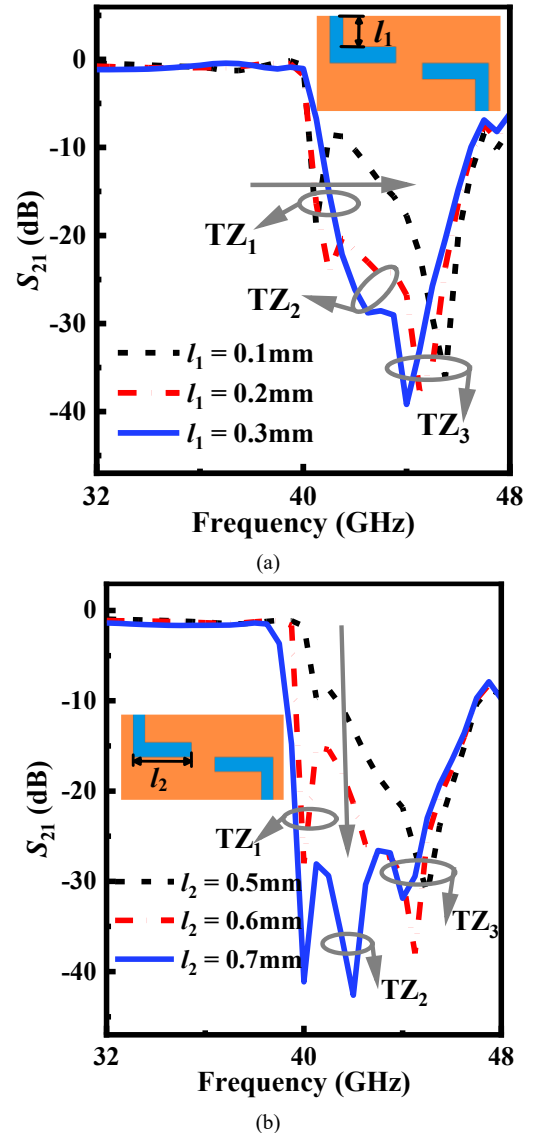


Fig. 7. Simulated  $S_{21}$  variations versus (a) parameter  $l_1$ , and (b) parameter  $l_2$ .



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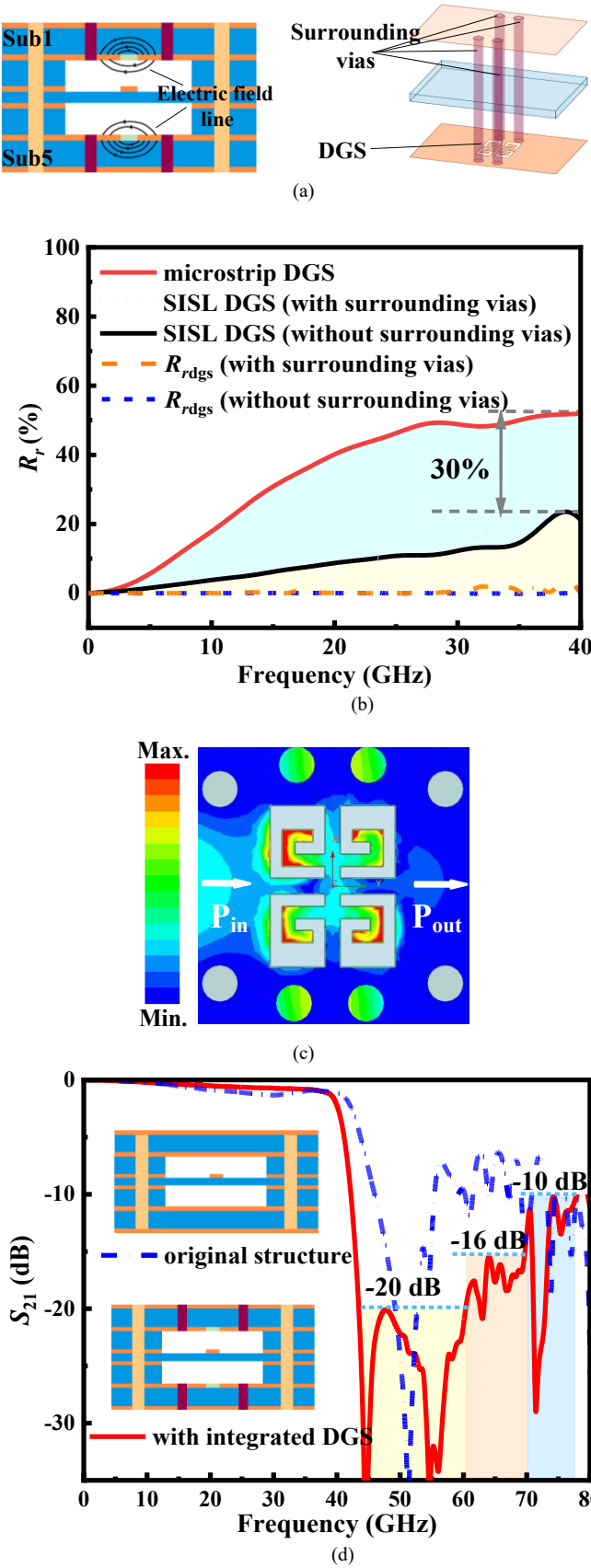


Fig. 8. (a) Structure of DGS shielded by metallic vias, (b) simulated results of radiation  $R_r$ , (c)  $E$ -field distribution diagram at 65GHz, and (d) simulated of  $S_{21}$  about stopband when compared to original structure.

It can be seen from Fig. 8(a) that DGS shielded by surrounding metallic vias and metal layer G1(G10) can confine the electric field lines between DGS and ground. And the metallic vias around DGS throughout Sub1 and Sub5 are used to prevent dissipation into the substrate. Since the radiation loss  $R_r$  can be calculated by the formula  $R_r = 1 - |S_{11}|^2 - |S_{21}|^2$ , which of SISL DGS (including the transition section from GCPW to SISL) is significantly reduced as shown in Fig. 8(b), especially the maximum  $R_r$  is reduced by 30% when compared to microstrip DGS. Furthermore, depending on the self-packaged characteristic of SISL, the radiation loss  $R_{rdgs}$  introduced only by the DGS tends to zero (excluding the GCPW-SISL transition section) as shown in Fig8(b), which confirms that integrating DGS on SISL can effectively reduce the radiation loss. It can be seen from the EM field distribution diagram at 65GHz in Fig.8(c) that four symmetrical "G-type" DGS cells integrated on the metal layer M2(M9) of SISL can effectively suppress the out-of-band stray resonance frequencies. Thus, the simulated stopband is finally extended to 60 GHz with  $S_{21}$  of -20 dB and further to 70 GHz with  $S_{21}$  of -16 dB when DGS structures are integrated on SISL as illustrated in Fig. 8(d).

### III. LPF MANUFACTURING, PACKAGING AND MEASUREMENT

The prototype of LPF is manufactured based on standard PCB process as shown in Fig. 9(a) and (b), and the physical size of the cavity is  $0.41\lambda_g \times 0.69\lambda_g \times 0.44\lambda_g$ , where  $\lambda_g$  represents the guided wavelength at 40GHz. The GCPW is employed as interface to carry out measurement based on our previous work on the GCPW to SISL transition structure [26]. Finally, the filter assembled with 2.92mm connectors, as illustrated in Fig. 9(c), is measured by R&S®ZNA67 vector network analyzer.

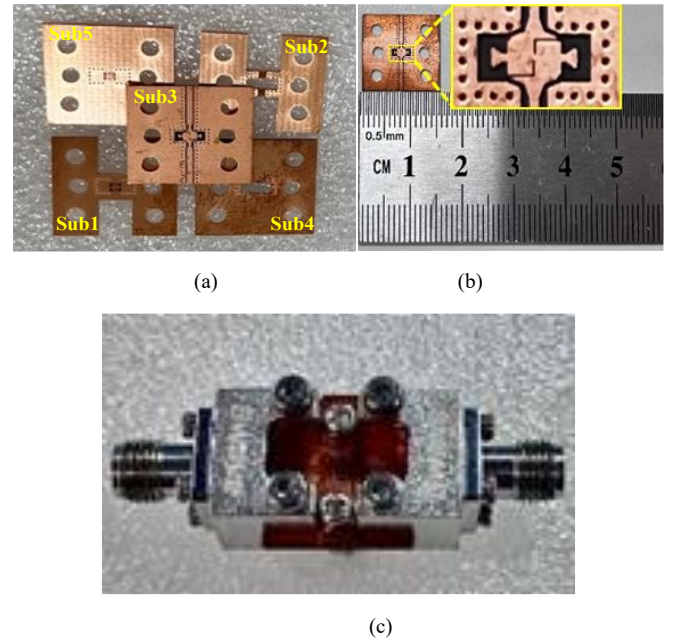


Fig. 9 Prototype of proposed LPF. (a) Whole structure, (b) details of LPF on Sub3, (c) assembly diagram. ( $a = 3.5\text{mm}$ ,  $c_1 = 1.69\text{mm}$ ,  $c_2 = 0.23\text{mm}$ ,  $c_3 = 0.17\text{mm}$ ,  $c_4 = 0.13\text{mm}$ ,  $m_1 = 0.13\text{mm}$ ,  $m_2 = 0.29\text{mm}$ ,  $m_3 = 0.45\text{mm}$ ,  $l_1 = 0.72\text{mm}$ ,  $l_2 = 0.55\text{mm}$ ,  $g_1 = 0.1\text{mm}$ ,  $l_2 = 0.55\text{mm}$ ,  $s_1 = 0.4\text{mm}$ ,  $s_2 = 0.2\text{mm}$ ,  $s_3 = 0.6\text{mm}$ ,  $s_4 = 0.15\text{mm}$ ,  $s_4 = 0.36\text{mm}$ ).

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It can be seen from Fig. 10 (a), the measured in-band  $IL$  of the LPF is no more than 1.85 dB from dc to 40 GHz and the measured in-band  $RL$  is better than 14.8 dB. The measured stopband with -17.2 dB rejection varies from 43GHz to 67GHz. For ultra-wideband filters applied in communication systems, a flat group delay is necessary because significant group delay

varying with frequency have a dispersion effect on the signal [12]. As shown in Fig. 10(b), the measured group delay  $\tau_g$  of the LPF in the passband is no more than 0.5 ns and relatively

Table I  
COMPARISON WITH OTHER PREVIOUS WORKS

Ref.	Technology	$f_c$ (GHz)	$IL$ (dB)	$RL$ (dB)	Size ( $\lambda_g^3$ )	R. C.	OS (dB)	SB (GHz)	Substrates	Self-packaging
[5]	Microstrip <sup>#1</sup>	dc-1	<2	>12	0.00038	1.2*	>30	1.6-6.5*	PET	No
[6]	Waveguide	10.3-12.6	<0.4	>15	5.09	1.02*	>60	13.7-43*	WR75	Yes
[10]	MCSICL <sup>#2</sup>	dc-30	<2.1	>10	0.42	1.17*	>35	36-60*	Rogers 5880	Yes
[12]	SISL	dc-18	<1	>12	0.282	1.07*	>30	19-26	Rogers 6002/6006	Yes
[13]	SISL	27.7-30.7	<1.6	>17	0.122	2	>80	35-65*	FR4	Yes
<b>This work</b>	<b>SISL</b>	<b>dc-40</b>	<b>&lt;1.85</b>	<b>&gt;14.8</b>	<b>0.124</b>	<b>1.09</b>	<b>&gt;17.2</b>	<b>43-67</b>	<b>FR4/ Rogers 5880</b>	<b>Yes</b>

Ref.: reference,  $f_c$ : cutoff frequency, R. C.: Rectangular Coefficient =  $|BW_{-30dB}/BW_{-3dB}|$ , OS: out-of-band suppression, SB: upper stopband, #1: microstrip based on polyimide film substrate, #2: condition of low pass part, \*: estimated value from figures.

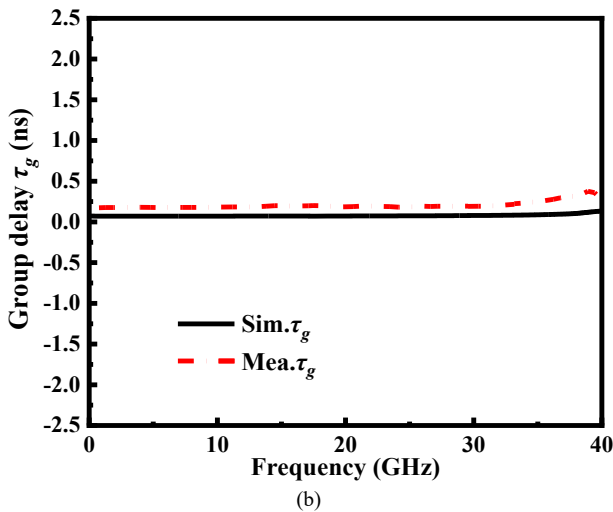
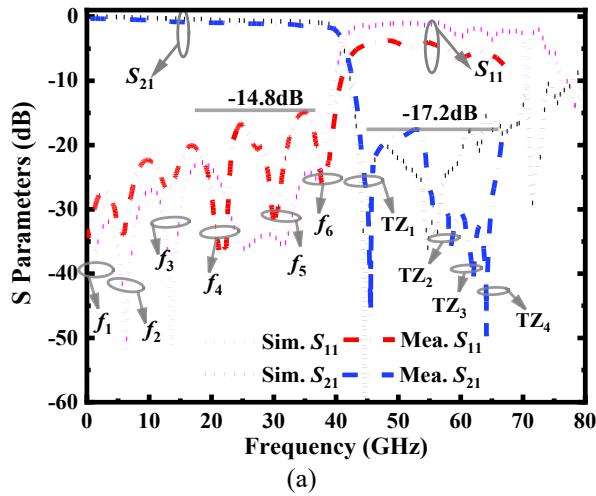


Fig. 10 Simulated and measured results of the proposed LPF. (a)  $S$  parameters of  $S_{11}$  and  $S_{21}$ , and (b) group delay  $\tau_g$ .

flat, which is in good agreement with the simulation ones. The inconsistencies between the simulated and measured results mainly caused by additional losses introduced by launch connectors, fabricating accuracy error and experimental assembly errors.

Table I shows the comparison of the proposed works with some typical works. Compared with the LPFs in Refs. [5], [6], [10], [12], the proposed LPF has the advantages of low loss and compact size. Compared to the bandpass filter in Ref. [13] which also excels in terms of  $IL$  and size, the proposed work has advantages in the aspect of operating bandwidth wider from dc-40 GHz and sharp roll-off skirt.

#### IV. CONCLUSION

In this brief, a dc-40 self-packaged compact GHz SISL LPF using ST-SIRs with low loss is proposed. The resonant characteristics of ST-SIRs are analyzed, and the cutoff frequency  $f_c$  can be adjusted flexibly by changing the physical sizes of ST-SIRs. Moreover, controllable TZs are introduced near the passband side to improve the frequency selectivity of the LPF by loading center-symmetric spurlines. The top and bottom shielding layers of SISL are also utilized to enhance the stopband of the LPF by integrating DGS structures. It is worth noting that utilizing the multi-layer characteristics of SISL to achieve multifunctional complex circuits may be a feasible trend. The proposed LPF is fabricated and measured, which is suitable for mm-wave communication applications requiring large bandwidth and high integration.

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